

Ultracold atom spin field effect transistors

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We propose a method of constructing cold atom analogs of the spintronic device known as the Datta-Das transistor (DDT), which despite its seminal conceptual role in spintronics, has never been successfully realized with electrons. We propose two alternative schemes for an atomic DDT, both of which are based on the experimental setup for tripod stimulated Raman adiabatic passage. Both setups involve atomic beams incident on a series of laser fields mimicking the relativistic spin orbit coupling for electrons that is the operating mechanism of the DDT.

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The emerging technology of semiconductor spintronics exploits the electron's spin degree of freedom, as well as its charge state. The first scheme for a semiconductor spintronic device was a spin field-effect transistor known as the Datta-Das transistor (DDT) (Fig. 1a) [1]. The eighteen years since the theoretical proposal have seen numerous experimental efforts to construct the DDT. Various experimental obstacles, such as difficulties in spin injection, stray electric fields and insufficient quality of spin-orbit coupling, have prevented successful implementation of the DDT [2].

In contrast to their electronic counterparts, cold atom systems are characterized by a high degree of controllability and tunability. This suggests the possibility of designing precise atomic analogs of electronic systems which, due either to fundamental physical limits or technological difficulties, are experimentally inaccessible in their original manifestations. The idea grows out of recent interest in "atomtronics," or constructing cold atom analogs of ordinary electronic materials, devices and circuits [3, 4, 5]. In particular, an atom diode has been proposed [3] and realized experimentally [5] using ultracold multilevel atom schemes.

In this paper, we identify a method for constructing a cold atom analog of a Datta-Das transistor. The setup is based on a four level "tripod" scheme of atom-light coupling [6, 7, 8, 9, 10] involving three atomic ground states and one excited state (see Fig. 1b). Such tripod schemes are an extension of the usual three-level Λ -type setup for stimulated Raman adiabatic passage (STIRAP) [3], and are experimentally accessible in metastable Ne, ⁸⁷Rb and a number of other gases [8, 9]. The proposed device provides a robust method for atomic state manipulation that is immune to the inhomogeneities intrinsic to programmed Rabi pulses.

The source terminal of an electronic DDT (Fig. 1a) is a ferromagnetic electrode that emits spin-polarized electrons as depicted in Fig. 1a. The DDT drain terminal is a ferromagnetic analyzer which acts as a spin filter. Between source and drain is a semiconducting gate region, within which the gate-induced electric field is trans-

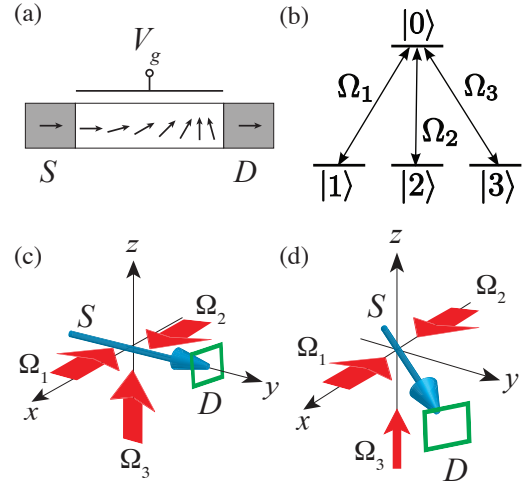


Figure 1: (a) Schematic of a DDT. "S" and "D" are ferromagnetic source and drain electrodes. In between is a semiconducting gate region, where the spin precesses by an amount which depends periodically on the tunable gate voltage V_g . This precession results in a controllable current modulation at D . (b) A tripod scheme of atomic energy levels, coupled by laser fields with Rabi frequencies Ω_i . (c,d) Two alternative setups for an atomic version of the DDT. Here, the source is a state-polarized atomic beam (blue), the gate is the intersection region of a configuration of laser beams (red), and the drain is an atomic state analyzer (green).

formed into an effective magnetic field, via Rashba spin-orbit coupling [11, 12]. While passing through the gate region, the electron's spin precesses, and the electron emerges at the drain having undergone a spin rotation which is tunable via the gate voltage. Since the drain passes only a certain spin direction, the drain current is an oscillating function of the gate voltage.

Our atomic analog of the DDT (Figs. 1c,d) uses a beam of atoms in place of electrons. The two dark states in the tripod setup play the role of the electron's spin states, and the "source" is a dilute atomic beam. The "gate" region consists of crossed laser beams engi-

neered to mimic Rashba or Rashba-like spin orbit couplings [13, 14, 15, 16, 17]; the analog of the gate voltage can be tuned by varying the relative strengths of the lasers. The drain is a state-selective atomic filter, such as a Stern-Gerlach device or radio-frequency or Raman outcoupler [18]. While the goal of this paper is to explore the possibility of constructing the atomic analog of spintronic devices, the two dark states of the tripod atom can be considered qubit states [19, 20, 21, 22]; in this context the atomic DDT represents a single-qubit phase gate for a dilute atomic beam. In contrast to typical single qubit gates, this setup does not involve time-dependent pulses, and the amount of the qubit rotation within the gate region is independent of the atom's velocity, due to the geometric nature of the process.

Tripod scheme The proposed DDT implementations are based on the tripod scheme (Fig. 1b-d), [6, 7, 8, 9, 10], in which a four level atom feels two counterpropagating stationary laser beams and a third orthogonal beam [14, 16, 17]. The lasers induce resonant transitions between the ground states $|j\rangle$ ($j = 1, 2, 3$) and an excited state $|0\rangle$, and have spatially dependent Rabi frequencies that can be parametrized as $\Omega_1 = \Omega\sqrt{1-\varepsilon^2}\cos\varphi e^{-i\kappa_0 x}$, $\Omega_2 = \Omega\sqrt{1-\varepsilon^2}\sin\varphi e^{i\kappa_0 x}$ and $\Omega_3 = \Omega\varepsilon e^{i\kappa_0 z}$, where κ_0 is the wave-number. The parameter $0 \leq \varepsilon \leq 1$ and the angle φ characterize the relative intensity of the three lasers.

In the interaction representation and rotating wave approximation, the electronic Hamiltonian of a tripod atom reads $\hat{H}_e = -\hbar\Omega|B\rangle\langle 0| + \text{H.c.}$, where $|B\rangle = (|1\rangle\Omega_1^* + |2\rangle\Omega_2^* + |3\rangle\Omega_3^*)/\Omega$. The Hamiltonian \hat{H}_e has two degenerate dark states $|D_j\rangle$ containing no excited state contribution and with zero energy: $\hat{H}_e|D_j\rangle = 0$, $j = 1, 2$. Additionally, a pair of bright eigenstates $|\pm\rangle = (|B\rangle \pm |0\rangle)/\sqrt{2}$ is separated from the dark states by $\mp\hbar\Omega$, where Ω is the Rabi frequency. For the light fields of interest, a set of dark states can be chosen as:

$$|D_1\rangle = (\sin\varphi|1\rangle' - \cos\varphi|2\rangle'), \quad (1)$$

$$|D_2\rangle = \varepsilon(\cos\varphi|1\rangle' + \sin\varphi|2\rangle') - \sqrt{1-\varepsilon^2}|3\rangle, \quad (2)$$

with $|1\rangle' = |1\rangle e^{i\kappa_0(z+x)}$ and $|2\rangle' = |2\rangle e^{i\kappa_0(z-x)}$. The dark states $|D_j\rangle \equiv |D_j(\mathbf{r})\rangle$ are space-dependent due to the spatial variation of the Rabi frequencies $\Omega_j \equiv \Omega_j(\mathbf{r})$. Since the incident light fields are stationary, both Ω_j and $|D_j\rangle$ are time-independent in the laboratory frame.

Let us adiabatically eliminate the bright states, so that the atom evolves within the dark-state manifold. In this limit the full atomic state vector can be expanded as $|\Psi(\mathbf{r}, t)\rangle = \sum_{n=1}^2 \chi_n(\mathbf{r}, t)|D_n(\mathbf{r})\rangle$, where a composite wavefunction $\chi_n(\mathbf{r}, t)$ describes the motion of an atom in the dark state $|D_n(\mathbf{r})\rangle$. The atomic center of mass motion is thus represented by a two-component wavefunction $\chi = (\chi_1, \chi_2)^T$ obeying the equation [10]

$$i\hbar\frac{\partial}{\partial t}\chi = \left[\frac{1}{2M}(-i\hbar\nabla - \mathbf{A})^2 + \Phi + V(\mathbf{r}) \right] \chi. \quad (3)$$

Here the 2×2 matrix \mathbf{A} with elements $\mathbf{A}_{n,m} = i\hbar\langle D_n(\mathbf{r})|\nabla D_m(\mathbf{r})\rangle$ is an effective vector potential known as the Mead-Berry connection [10, 23, 24, 25]. The light field configuration we have chosen yields

$$\mathbf{A}_{11} = -\hbar\kappa_0(\mathbf{e}_z - \cos(2\varphi)\mathbf{e}_x), \quad (4)$$

$$\mathbf{A}_{12} = -\hbar\varepsilon(\kappa_0\sin(2\varphi)\mathbf{e}_x + i\nabla\varphi), \quad (5)$$

$$\mathbf{A}_{22} = -\hbar\kappa_0\varepsilon^2(\mathbf{e}_z + \cos(2\varphi)\mathbf{e}_x). \quad (6)$$

with \mathbf{e}_x and \mathbf{e}_z being the unit Cartesian vectors. The 2×2 matrix Φ with elements $\Phi_{nm} = (\hbar^2/2M)\langle D_n(\mathbf{r})|\nabla B(\mathbf{r})\rangle\langle B(\mathbf{r})|\nabla D_m(\mathbf{r})\rangle$ is the Born-Huang scalar potential. Both \mathbf{A} and Φ emerge due to the spatial dependence of the atomic dark states. Here also $V(\mathbf{r})$ is an external trapping potential which will be neglected because of our interest in free atomic motion.

Suppose the atoms in the beam have a velocity \mathbf{v} much larger than the recoil velocity $v_{\text{rec}} = \hbar\kappa_0/M \approx 0.5\text{cm/s}$ for ^{87}Rb . In this limit, the atomic velocity does not change significantly when crossing the laser beams, and a simplified semiclassical approach with no reflected waves can be used. To this end, let us let us apply a gauge transformation $\chi(\mathbf{r}, t) = e^{iM\mathbf{v}\cdot\mathbf{r}/\hbar - iM\mathbf{v}^2 t/2\hbar}\tilde{\chi}(\mathbf{r}, t)$, implying transition to a reference frame moving with velocity \mathbf{v} , where the envelope function $\tilde{\chi}$ varies slowly with \mathbf{r} over the atom's wavelength $\lambda = h/(Mv)$. Keeping only the terms containing the velocity \mathbf{v} (or time derivatives), one arrives at the following approximate equation for $\tilde{\chi}$:

$$i\hbar(\partial/\partial t + \mathbf{v}\cdot\nabla)\tilde{\chi}(\mathbf{r}, t) = -\mathbf{v}\cdot\mathbf{A}(\mathbf{r})\tilde{\chi}(\mathbf{r}, t). \quad (7)$$

As the omitted Born-Huang potential Φ and the A^2 term are of the order of the recoil energy $\hbar\omega_{\text{rec}} = \hbar^2\kappa_0^2/2M \ll Mv^2/2$, the fast moving atoms will not feel these potentials. For incident velocities v of the order of v_{rec} or smaller, the atomic motion will undergo a complex *Zitterbewegung* type motion [15, 26] which is beyond the scope of the present study.

Assuming that $\mathbf{v}\cdot\mathbf{A}$ commutes with itself at different times, by going to a moving frame of reference $\mathbf{r}' = \mathbf{r} - \mathbf{v}t$, we can relate the wavefunction $\tilde{\chi}$ at time $t = t_f$ to that at a previous time $t = t_i$, through

$$\tilde{\chi}(\mathbf{r}', t_f) = \exp(i\Theta)\tilde{\chi}(\mathbf{r}', t_i). \quad (8)$$

The matrix $\Theta = -\hbar^{-1}\int_{t_i}^{t_f}\mathbf{A}(\mathbf{r}' + \mathbf{v}t)\cdot\mathbf{v}dt$ is a 2×2 Hermitian matrix describing evolution of the atomic state. It can be represented in terms of the integration over the path from $\mathbf{r}_i = \mathbf{r}' + \mathbf{v}t_i$ to $\mathbf{r}_f = \mathbf{r}' + \mathbf{v}t_f$:

$$\Theta = -\frac{1}{\hbar}\int_{\mathbf{r}_i}^{\mathbf{r}_f}\mathbf{A}(\mathbf{r})\cdot d\mathbf{r}. \quad (9)$$

Our analysis of the atomic dynamics will be based on Eqs. (8)-(9) and (4)-(6).

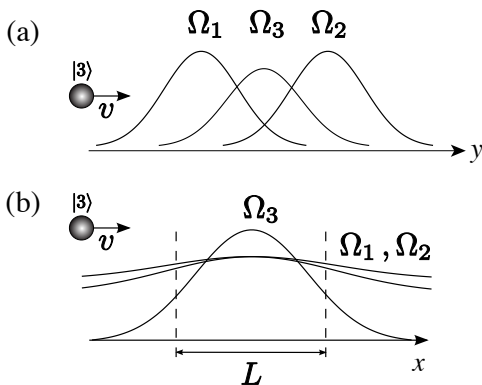


Figure 2: Schematics of the first (a) and second (b) setups for an atomic transistor: The atom, along its trajectories (shown in Figs. 1c,d) sees the above profile of laser fields.

Atomic analogs of the DDT We first consider the setup depicted in Figs. 1c and 2a. The atoms are incident along the y axis, along which laser beams 1 and 2 are shifted relative to each other [6, 7, 8], so that

$$A_y = \hbar\sigma_y\varepsilon(y)\partial\varphi(y)/\partial y. \quad (10)$$

Equations (10) and (9) generate the evolution matrix

$$\Theta = \alpha\sigma_y, \quad \alpha = -\int_{y_i}^{y_f} \varepsilon(y) \frac{\partial}{\partial y} \varphi(y) dy, \quad (11)$$

where α is the mixing angle and σ_y is the usual Pauli matrix. By taking the initial and final times to be sufficiently large, we have $y_i \rightarrow -\infty$ and $y_f \rightarrow +\infty$.

As Figs. 1c and 2a show, the first laser beam is dominant as the atom enters the gate region, while the second one dominates as it exits. In between, the atom feels the third beam. This configuration results in a gate-induced rotation of the atom's internal state, by a mixing angle α . Specifically, suppose the atom enters the gate region in the state $\tilde{\chi}(\mathbf{r}')|3\rangle$ (initially, $|3\rangle = -|D_2(\mathbf{r}', t_i)\rangle$). The atom exits the gate region in the state

$$\tilde{\Psi}(\mathbf{r}', t_f) = -\tilde{\chi}(\mathbf{r}') \begin{pmatrix} \sin \alpha \\ \cos \alpha \end{pmatrix}, \quad (12)$$

where $\cos^2 \alpha$ represents the probability that the atom will emerge in state $|3\rangle$. This gate-controlled state rotation is an atomic analog of the DDT. The mixing angle α is controlled by the relative amplitude of the third laser $\eta = |\Omega_3|/|\Omega_1|$ at the central point, as shown in Fig. 3. Thus, η plays the role of the gate voltage V_g in Fig. 1a.

A point of particular importance is that, as in the electronic DDT, the mixing angle α and hence the transmission coefficient $\cos \alpha$ are independent of the velocity of the incident beam, meaning that the transistor properties are preserved under a spread in atomic velocities.

Since $\varepsilon(y) \leq 1$, the mixing angle given by Eq. (11) ranges from 0 to $\pi/2$, so the sensitivity $|\Delta\alpha|/|\Delta\eta|$ of

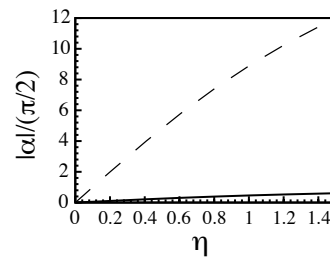


Figure 3: The mixing angle α vs. the relative amplitude of the third field η for the first (solid line) and the second (dashed line) setups. The amplitudes of the beams are Gaussian: $|\Omega_1| = a \exp(-(u+\delta)^2/w_1^2)$, $|\Omega_2| = a \exp(-(u-\delta)^2/w_2^2)$, and $|\Omega_3| = a\eta \exp(-u^2/w_3^2 - \delta^2/w^2)$, with $u = y$ (first setup) or $u = x$ (second setup). In the first setup, $w_1 = w_2 = w_3 = \delta = 2\lambda$, with $\lambda = 600$ nm being the laser wave length. For the second setup, all the beams are centered at the same point ($\delta = 0$) and have the widths $w_1 = w_2 = 10w_3 = 20\lambda$.

the DDT is on the order of unity. Small changes in the relative Rabi frequency η will thus lead to small changes in the mixing angle: $|\Delta\alpha| \sim |\Delta\eta|$. We next analyze an alternative setup which enables us to create a more sensitive DDT.

Now suppose that the first two light beams counterpropagate along the x axis with equal intensities (Fig. 1d), i.e., $\varphi = \pi/4$ in Eqs. (4)-(6) for \mathbf{A} . The light-induced vector potential then resembles the Rashba spin orbit coupling which is the spin rotation mechanism of the Datta-Das transistor:

$$A_z = -\frac{\hbar\kappa_0}{2}(1 - \varepsilon^2)\sigma_z \quad (13)$$

$$A_x = -\hbar\kappa_0\varepsilon\sigma_x, \quad A_y = 0. \quad (14)$$

We have removed a term proportional to the identity matrix in A_z via the trivial gauge transformation $\exp[i\hbar\kappa_0(1 + \varepsilon^2)z\mathbf{I}]$.

The atomic beam crosses the laser beams at an angle in the $x - y$ plane, with initial velocity components $v_x \neq 0$ and v_y . Since $A_y = 0$, the motion in the y direction has no effect on the state rotation; however, sending the beam in at an angle removes the experimental difficulty of having the atoms incident from the same direction as the laser beams. Along its trajectory, the atom feels the laser beam profile illustrated schematically in Fig. 2b. The evolution matrix of Eq. (9) is then

$$\Theta = \alpha\sigma_x, \quad \alpha = \kappa_0 \int_{x_i}^{x_f} \varepsilon(x) dx, \quad (15)$$

where α is the mixing angle, and σ_x the usual Pauli matrix. The initial and final times are taken to be sufficiently large that the spatial integration runs from $x_i = -\infty$ to $x_f = +\infty$.

As in the previous scheme, the intensity of the third laser vanishes ($\varepsilon \rightarrow +0$) away from the gate region (see

Fig. 2b). Only the intensity of the third laser has significant spatial dependence inside the gate region, the intensities of the first two lasers being nearly constant there. The controlled state rotation in this case is driven by the *phases* of the counterpropagating laser beams, rather than by variations of beam intensities.

As in the previous setup, the atom enters the gate region in the state $|\tilde{\Psi}(\mathbf{r}', t_i)\rangle = -\tilde{\chi}(\mathbf{r}')|3\rangle = -\tilde{\chi}(\mathbf{r}')|D_2(\mathbf{r}', t_i)\rangle$, and exits in a rotated state

$$\tilde{\Psi}(\mathbf{r}', t_f) = -\tilde{\chi}(\mathbf{r}') \begin{pmatrix} i \sin \alpha \\ \cos \alpha \end{pmatrix}, \quad (16)$$

This rotation is, again, an analog of the spin rotation of the DDT [1]; here the mixing angle α is controlled by the variation of the relative intensity of the third laser beam.

To estimate the mixing angle, suppose that the Rabi frequency Ω_3 (and hence the dimensionless parameter ε) does not change considerably within the gate region. Equation (15) then gives the following estimate of the mixing angle: $\alpha = \kappa_0 \bar{\varepsilon} L$, where L (see Fig. 2b) is the length of the area in which the third laser has the strongest intensity. Note that the mixing angle is now proportional to the length L , as well as to the average strength $\kappa_0 \bar{\varepsilon}$ of the spin-orbit coupling. This behavior is in direct analogy to the DDT involving the electron spin [1]. As in Eq. (2) of [1], the output power of the atoms in the internal state $|3\rangle$ is given by $P = \cos^2 \alpha = \cos^2(\kappa_0 \bar{\varepsilon} L)$. Using such an atomic setup the mixing angle $\alpha = \kappa_0 \bar{\varepsilon} L$ can be much larger than $\pi/2$, provided $L \gg (\kappa_0 \bar{\varepsilon})^{-1}$, as one can see in Fig. 3. Small changes in the relative amplitude of the third laser $\eta = |\Omega_3|/|\Omega_1|$ can, therefore, provide substantial changes in the mixing angle: $|\Delta\alpha| \sim |\Delta\eta| \kappa_0 L$. The sensitivity of such a DDT, $|\Delta\alpha|/|\Delta\eta| \sim \kappa_0 L$, can far exceed unity if L is much greater than the optical wave-length $\lambda = 2\pi/\kappa_0$.

Finally, we address the experimental feasibility of both schemes, and estimate the required velocity of the atomic beam. The atom crosses the gate region in a time $\tau = L/v$. Due to their nonadiabatic coupling to the bright states, the dark state atoms have the finite lifetime $\tau_D = \Omega^2/\gamma\Delta\omega^2$ [27] where γ is the excited state decay rate and $\Delta\omega = v\partial\varphi/\partial y \sim v\pi/L$ (first setup), or $\Delta\omega = v\kappa_0$ (second setup). To avoid decay, we require the beam to be in the adiabatic limit, i.e. $\tau/\tau_D \ll 1$. Taking $\Omega = 2\pi \times 10^7$ Hz [28], $\gamma = 10^7$ s⁻¹, $\kappa_0 = 2\pi/\lambda$, $\lambda = 600$ nm and $L = 4\lambda$, we require atomic velocities $v \ll 100$ m/s for the first setup and $v \ll 1$ m/s for the second one. The increased sensitivity in the second scheme thus comes at the expense of increased non-adiabatic losses.

Because ultracold atoms are highly tunable and controllable, they can serve as quantum simulators for a variety of other systems, including systems which have yet to be experimentally accessed in their original manifestations. In this paper, we have identified an atomic analog of one such system, the spin field-effect transistor. Like their electronic counterpart, our atomic transistors pro-

vide controllable state manipulation that is relatively insensitive to the thermal spread of beam velocities. The devices we have proposed are based on the familiar tripod STIRAP configuration, and appear to be feasible within current experimental procedures.

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